

MOSFET TECHNOLOGY FOR PROGRAMMABLE ADDRESS DECODE AND CORRECTION

Abstract of the Disclosure

5 An illustrative embodiment of the present invention includes a non-volatile, reprogrammable circuit switch. The circuit switch includes a metal oxide semiconductor field effect transistor (MOSFET) in a substrate. The MOSFET has a source region, a drain region, a channel region between the source and drain regions, and a gate separated from the channel region by a gate oxide. According
10 to the teachings of the present invention, the MOSFET is a programmed MOSFET having a charge trapped in the gate oxide adjacent to the source region such that the channel region has a first voltage threshold region (V_{t1}) and a second voltage threshold region (V_{t2}).

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